

## PRELIMINARY

## M63840P/FP/KP

8-Unit 500mA Source Type Darlington Transistor-Array With Clamp Diode

\* Notice: This is not a final specification.  
Some parametric limits are subject to change.

## DESCRIPTION

M63840P/FP/KP are eight-circuit output-sourcing Darlington transistor array. The circuits are made of PNP and NPN transistors. Both the semiconductor integrated circuits perform high-current driving with extremely low input-current supply.

## FEATURES

- High breakdown voltage ( $BV_{CEO} \geq 40V$ )
- High-current driving ( $I_o(max) = -500mA$ )
- With output clamping diodes
- Driving available with TTL output or C-MOS IC output
- Wide operating temperature range ( $T_a = -40\sim+85^{\circ}C$ )
- Output current-sourcing type

## APPLICATION

Drives of relays, printers, LEDs, fluorescent display tubes and lamps, and interfaces between MOS-bipolar logic systems and relays, solenoids, of small motors.

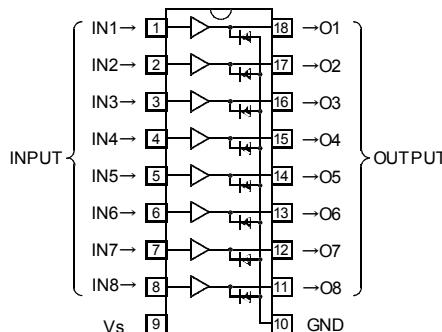
## FUNCTION

The M63840P/FP/KP each have eight circuits, which are made of input inverters and current-sourcing outputs. The output are made of PNP transistors and NPN Darlington transistors. The PNP transistor base current is constant. A clamping diode is provided between each output and GND. Vs and GND are used commonly among the eight circuits.

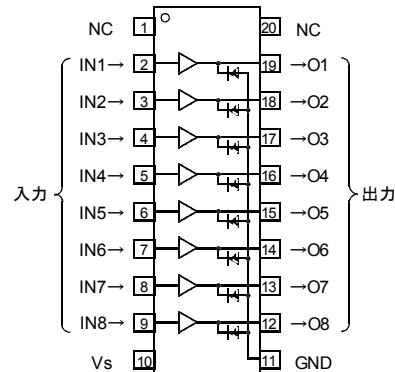
The inputs have resistance of  $10k\Omega$ , and voltage of up to 15V is applicable. Output current is 500mA maximum. Supply voltage Vs is 40V maximum.

The M63840P/FP/KP is enclosed in a molded small flat package, enabling space-saving design.

## PIN CONFIGURATION (TOP VIEW)

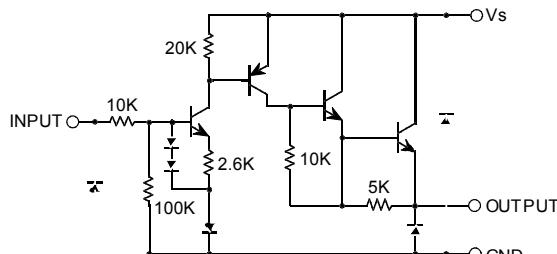


Package type 18P4G(P)

Package type 20P2N-A(FP)  
20P2E-A(KP)

NC: No connection

## CIRCUIT DIAGRAM (EACH CIRCUIT)



The eight circuits share Vs and GND.

The diode, indicated with the dotted line, is parasitic, and cannot be used.

Unit:  $\Omega$

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ABSOLUTE MAXIMUM RATINGS (Unless otherwise noted,  $T_a = -40 \sim +85^\circ\text{C}$ )

Symbol	Parameter	Conditions	Ratings	Unit
$V_{CEO}$	Collector-emitter voltage	Output, L	-0.5 ~ +40	V
$V_s$	Supply voltage		40	V
$V_i$	Input voltage		-0.5 ~ +15	V
$I_o$	Output current	Current per circuit output, H	-500	mA
$I_F$	Clamping diode forward current		-500	mA
$V_R$	Clamping diode reverse voltage		35	V
$P_d$	Power dissipation	$T_a = 25^\circ\text{C}$ , when mounted on board	M63840P	1.79
			M63840FP	1.10
			M63840KP	0.68
$T_{opr}$	Operating temperature		-40 ~ +85	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55 ~ +125	$^\circ\text{C}$

RECOMMENDED OPERATING CONDITIONS (Unless otherwise noted,  $T_a = -40 \sim +85^\circ\text{C}$ )

Symbol	Parameter	Limits			Unit
		min	typ	max	
$V_s$	Supply voltage	0	-	40	V
$I_o$	Output current (Current per 1 circuit when 8 circuits are coming on simultaneously)	Duty Cycle P: no more than 10% FP: no more than 5% KP: no more than 3%	0	-	-350
		Duty Cycle P: no more than 54% FP: no more than 30% KP: no more than 18%	0	-	-100
$V_{IH}$	"H" input voltage	2.0	-	12	V
$V_{IL}$	"L" input voltage	0	-	0.8	V

ELECTRICAL CHARACTERISTICS (Unless otherwise noted,  $T_a = 25^\circ\text{C}$ )

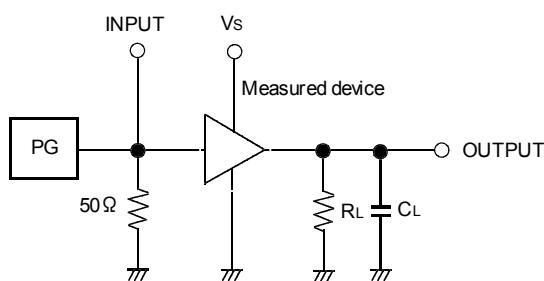
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
$I_{S(\text{leak})}$	Supply leak current	$V_s = 40\text{V}$ , $V_i = 0.8\text{V}$	-	-	100	$\mu\text{A}$
$V_{CE(\text{sat})}$	Collector-emitter saturation voltage	$V_s = 10\text{V}$ , $V_i = 2\text{V}$ , $I_o = -350\text{mA}$	-	1.7	2.0	V
		$V_s = 10\text{V}$ , $V_i = 2\text{V}$ , $I_o = -100\text{mA}$	-	1.5	1.8	
$I_i$	Input current	$V_i = 2.4\text{V}$	-	36	52	$\mu\text{A}$
		$V_i = 3.85\text{V}$	-	180	260	
$I_s$	Supply current	$V_s = 40\text{V}$ , $V_i = 2\text{V}$ (per 1 circuit)	-	-	2.5	mA
$V_F$	Clamping diode forward voltage	$I_F = 350\text{mA}$	-	1.3	2.0	V
$I_R$	Clamping diode reverse current	$V_R = 40\text{V}$	-	-	100	$\mu\text{A}$

SWITCHING CHARACTERISTICS (Unless otherwise noted,  $T_a = 25^\circ\text{C}$ )

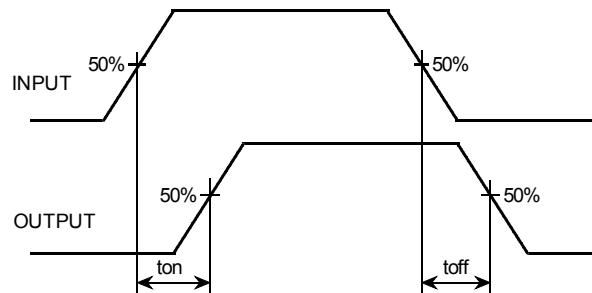
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
$t_{on}$	Turn-on time	$C_L = 15\text{pF}$ (note 1)	-	180	-	ns
			-	2200	-	ns
$t_{off}$	Turn-off time					

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## NOTE 1 TEST CIRCUIT



## TIMING DIAGRAM



(1) Pulse generator (PG) characteristics: PRR = 1KHz,

tw = 10 μs, tr = 6ns, tf = 6ns, Zo = 50Ω,

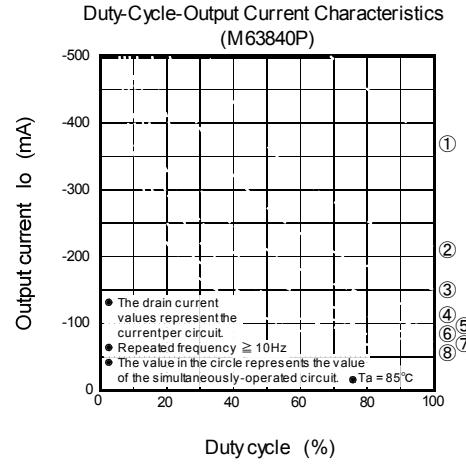
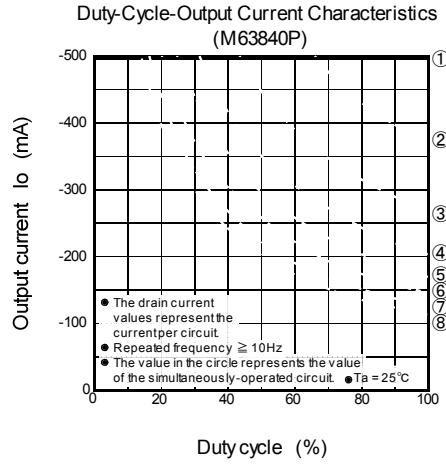
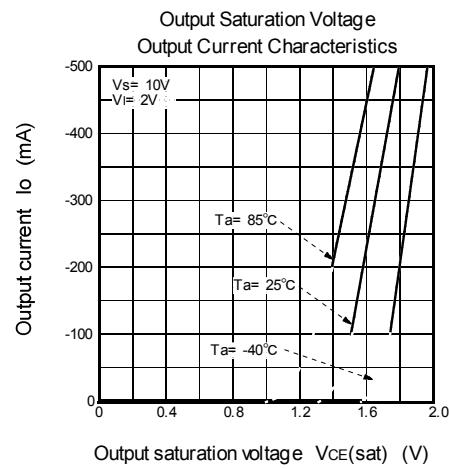
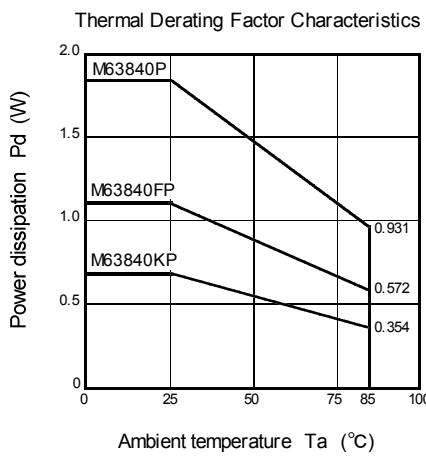
Vi = 0~2.4V

(2) Input-output conditions: RL = 100Ω, Vs = 40V

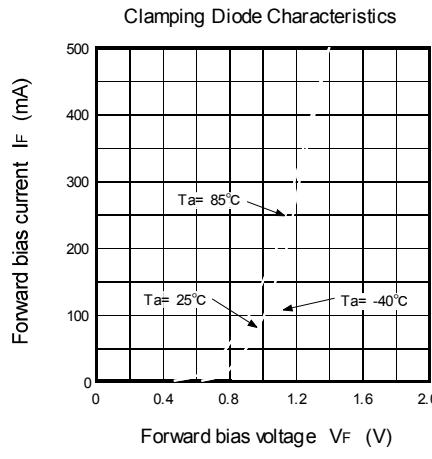
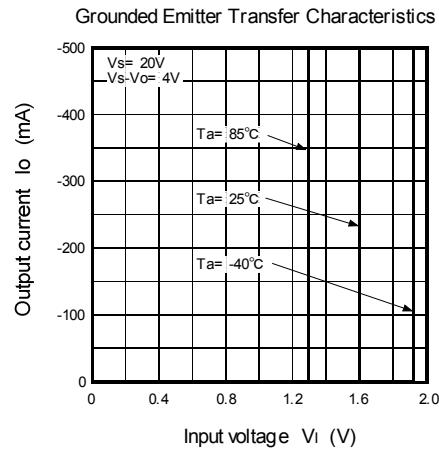
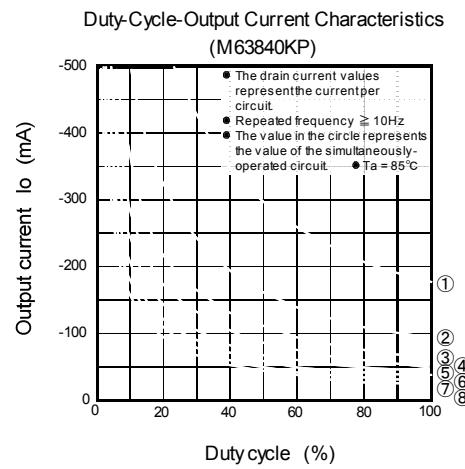
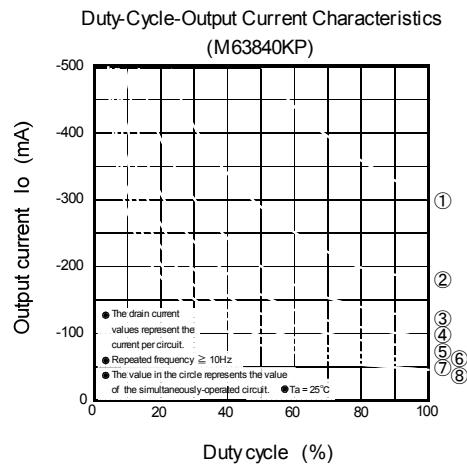
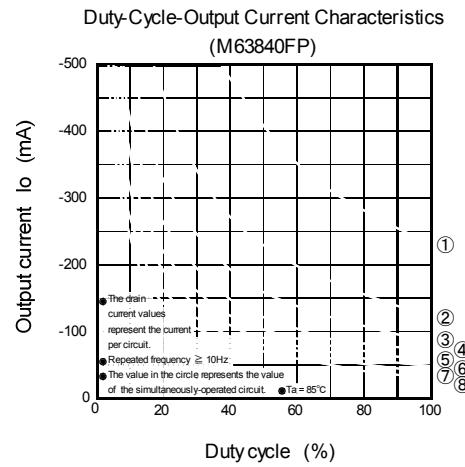
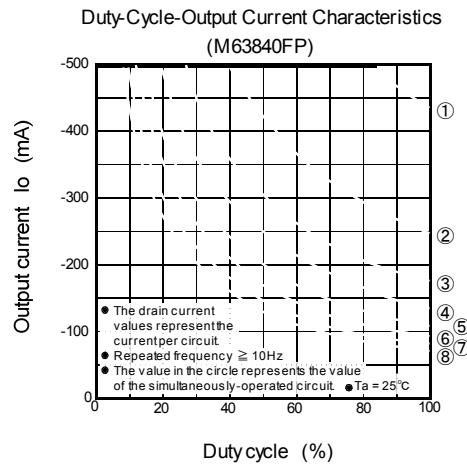
(3) Electrostatic capacity CL includes floating capacitance

at connections and input capacitance at probes.

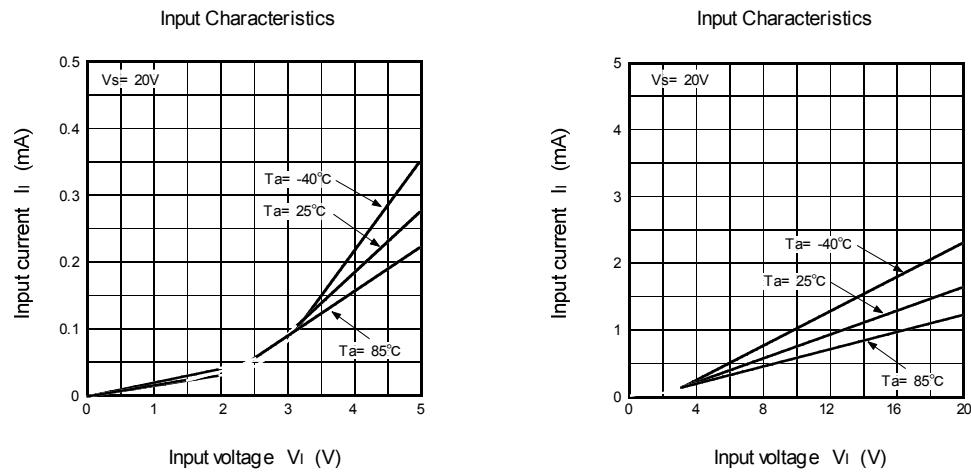
## TYPICAL CHARACTERISTICS



## 8-Unit 500mA Source Type Darlington Transistor-Array With Clamp Diode



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**18P4G**

Plastic 18pin 300mil DIP

EIAJ Package Code	JEDEC Code	Weight(g)	Lead Material
DIP18-P-300-2.54	-	1.3	Cu Alloy

Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	-	-	4.5
A1	0.51	-	-
A2	-	3.3	-
b	0.4	0.5	0.6
b1	1.1	1.2	1.5
c	0.2	0.25	0.32
D	23.8	24.0	24.2
E	6.15	6.3	6.45
[e]	-	2.54	-
[e1]	-	7.62	-
L	3.0	-	-
$\theta$	0°	-	15°

**20P2N-A**

(MMP)

Plastic 20pin 300mil SOP

EIAJ Package Code	JEDEC Code	Weight(g)	Lead Material
SOP20-P-300-1.27	-	0.26	Cu Alloy

Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	-	-	2.1
A1	0	0.1	0.2
A2	-	1.8	-
b	0.35	0.4	0.5
c	0.18	0.2	0.25
D	12.5	12.6	12.7
E	5.2	5.3	5.4
[e]	-	1.27	-
HE	7.5	7.8	8.1
L	0.4	0.6	0.8
L1	-	1.25	-
[Z]	-	0.585	-
Z1	-	-	0.735
x	-	-	0.25
y	-	-	0.1
$\theta$	0°	-	8°
b2	-	0.76	-
[e1]	-	7.62	-
I2	1.27	-	-

## 8-Unit 500mA Source Type Darlington Transistor-Array With Clamp Diode

**20P2E-A**